

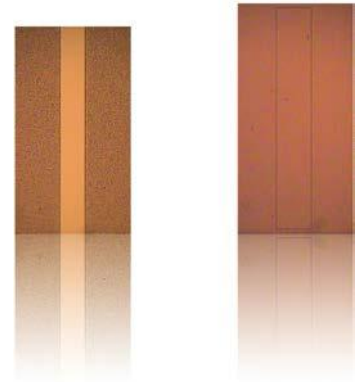
Diode Laser Unmounted Single Emitters and Bars

808nm 2W Unmounted Single Emitter

Semiconductor lasers are the centerpiece of most of today's industrial laser systems. Whether direct material processing or optical pumping of solid-state lasers, fiber lasers or disc lasers, the unmounted single emitters and bars are the key component for the initial conversion of electrical energy into light.

HTOE has been focusing on the semiconductor wafer technology from 1998, delivers the multimode high power at wavelengths between 635 and 1064nm.

- High Power multimode unmounted bars up to 40W CW and 200W QCW output
- Unmounted single emitters up to 2W CW Power
- Available wavelengths include 635nm, 650nm, 808nm, 980nm and 1064nm



Parameters (25°C)

Parameter		Unit	CLDM-0808-2000-02
Optical Parameter	Output Power P_o	mW	2000
	Center Wavelength λ_c	nm	808 ± 5
	Beam Divergence $\theta_{\perp} \times \theta_{//}$	deg	38x10
	COD	W	≥ 4.00
Geometrical	Emitter Width	μm	100/150
	Width	μm	500
	Cavity Length	μm	1500/1000
Electrical Parameter	Slope Efficiency E_s	W/A	≥ 1.15
	Threshold Current I_{th}	A	≤ 0.6
	Operating Current I_f	A	≤ 2.3
	Operating Voltage V_f	V	≤ 2



Notice

1. Item notice: CLDM(item model)-****(center wavelength)-****(output power)-02.
2. Data sheet is based on the result of testing under 25°C.
3. Data sheet is based on the C-Mount package testing.
4. For more information, please contact Hi-Tech Optoelectronics Co., Ltd.

